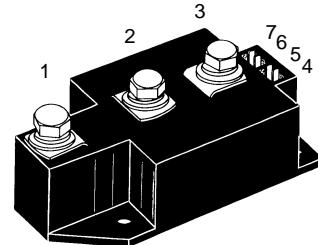


Thyristor Modules

Thyristor/Diode Modules

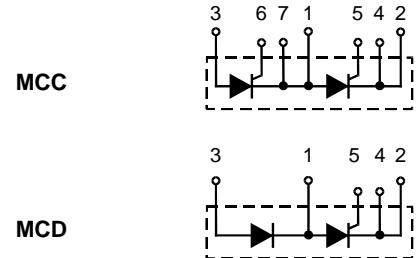
I_{TRMS} = 2x 400 A
I_{TAVM} = 2x 250 A
V_{RRM} = 800-1600 V

V _{RSM} V _{DSM}	V _{RRM} V _{DRM}	Type	
V	V	Version 1	Version 1
900	800	MCC 220-08io1	MCD 220-08io1
1300	1200	MCC 220-12io1	MCD 220-12io1
1500	1400	MCC 220-14io1	MCD 220-14io1
1700	1600	MCC 220-16io1	MCD 220-16io1



Symbol	Test Conditions	Maximum Ratings	
I _{TRMS} , I _{FRMS}	T _{VJ} = T _{VJM}	400	A
I _{TAVM} , I _{FAVM}	T _C = 85°C; 180° sine	250	A
I _{TSM} , I _{FSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	8500 A 9000 A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	7000 A 7600 A
$\int i^2 dt$	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	360 000 A ² s 336 000 A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	245 000 A ² s 240 000 A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 μs V _D = 2/3 V _{DRM} I _G = 1 A di _G /dt = 1 A/μs	repetitive, I _T = 750 A non repetitive, I _T = 250 A	100 A/μs 800 A/μs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000 V/μs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 μs t _p = 500 μs	120 W 60 W 20 W
P _{GAV}			10 V
V _{RGM}			
T _{VJ}		-40...+140	°C
T _{VJM}		140	°C
T _{stg}		-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	3000 V~ 3600 V~
M _d	Mounting torque (M5) Terminal connection torque (M8)		2.5-5/22-44 Nm/lb.in. 12-15/106-132 Nm/lb.in.
Weight	Typical including screws	320	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions



Features

- International standard package
- Direct copper bonded Al₂O₃ -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Keyed gate/cathode twin pins

Applications

- Motor control
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Contactless switches

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Test Conditions	Characteristic Values	
I_{RRM}	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$	70	mA
I_{DRM}		40	mA
V_T, V_F	$I_T, I_F = 600 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	1.53	V
V_{TO}	For power-loss calculations only ($T_{VJ} = 140^\circ\text{C}$)	0.9	V
r_T		1.0	$\text{m}\Omega$
V_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	2	V
	$T_{VJ} = -40^\circ\text{C}$	3	V
I_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	150	mA
	$T_{VJ} = -40^\circ\text{C}$	200	mA
V_{GD}	$T_{VJ} = T_{VJM}$; $V_D = 2/3 V_{DRM}$	0.25	V
I_{GD}		10	mA
I_L	$T_{VJ} = 25^\circ\text{C}$; $t_p = 30 \mu\text{s}$; $V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}$; $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	200	mA
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$	150	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = 1/2 V_{DRM}$ $I_G = 1 \text{ A}$; $di_G/dt = 1 \text{ A}/\mu\text{s}$	2	μs
t_q	$T_{VJ} = T_{VJM}$; $I_T = 300 \text{ A}$, $t_p = 200 \mu\text{s}$; $-di/dt = 10 \text{ A}/\mu\text{s}$ typ. $V_R = 100 \text{ V}$; $dv/dt = 50 \text{ V}/\mu\text{s}$; $V_D = 2/3 V_{DRM}$	200	μs
Q_s	$T_{VJ} = 125^\circ\text{C}$; $I_T, I_F = 400 \text{ A}$, $-di/dt = 50 \text{ A}/\mu\text{s}$	760	μC
I_{RM}		275	A
R_{thJC}	per thyristor/diode; DC current	0.139	K/W
	per module	0.0695	K/W
R_{thJK}	per thyristor/diode; DC current	0.179	K/W
	per module	0.0895	K/W
d_s	Creepage distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s^2

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

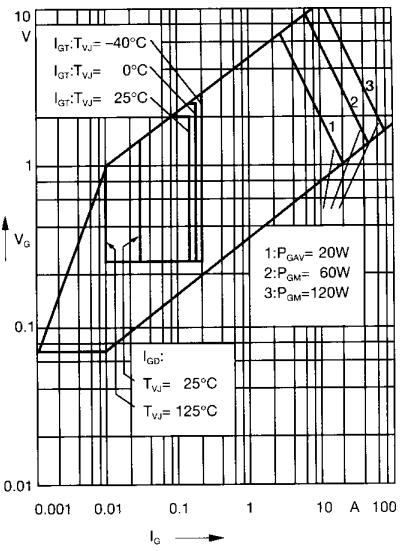
Type **ZY 180L** (L = Left for pin pair 4/5) } UL 758, style 1385,
Type **ZY 180R** (R = right for pin pair 6/7) } CSA class 5851, guide 460-1-1

Fig. 1 Gate trigger characteristics

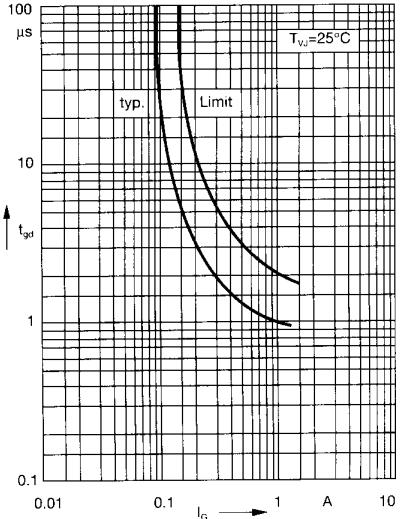
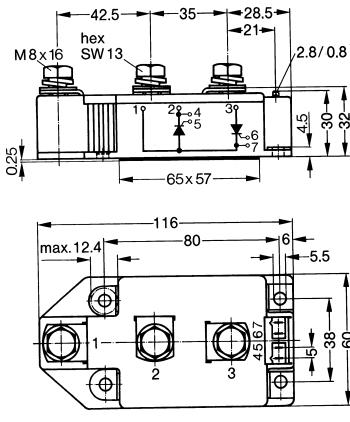


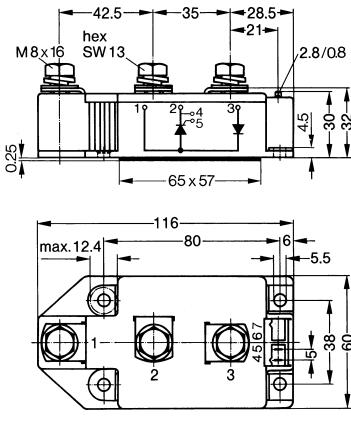
Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

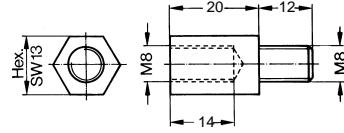
MCC



MCD



Threaded spacer for higher Anode/Cathode construction:
Type **ZY 250**, material brass



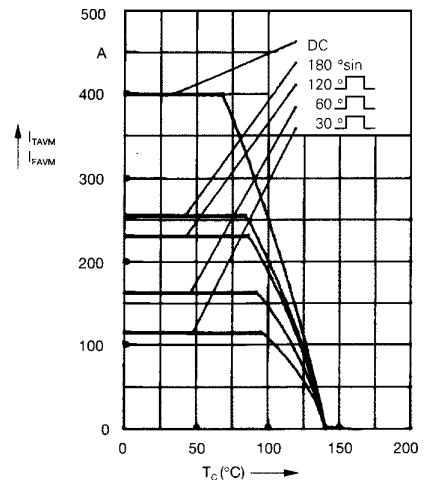
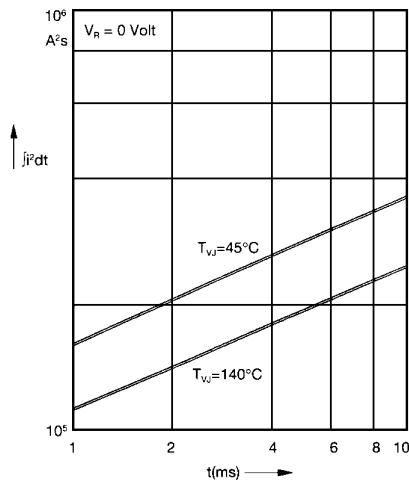
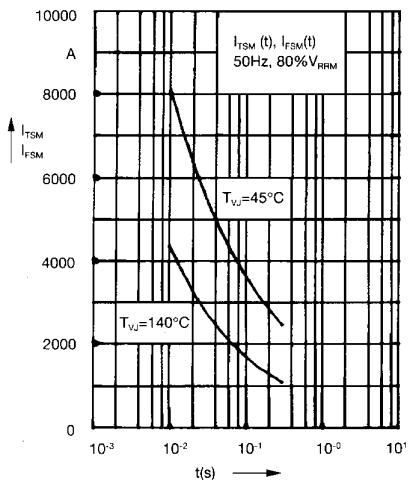
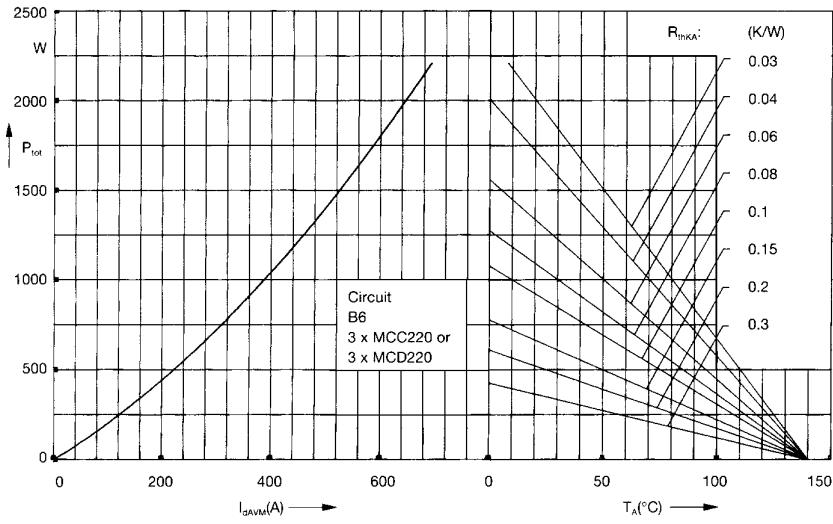
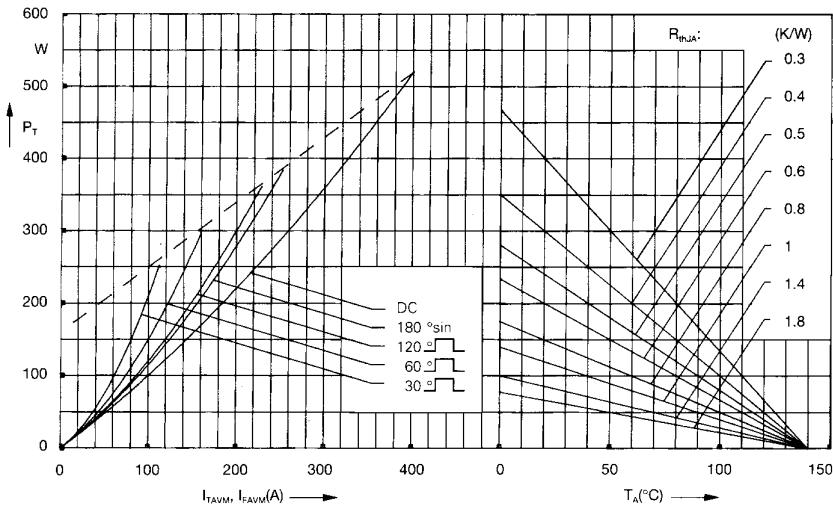


Fig. 3 Surge overload current
 I_{TSM}, I_{FSM} : Crest value, t : duration

Fig. 4 $\int i^2 dt$ versus time (1-10 ms)

Fig. 4a Maximum forward current at case temperature



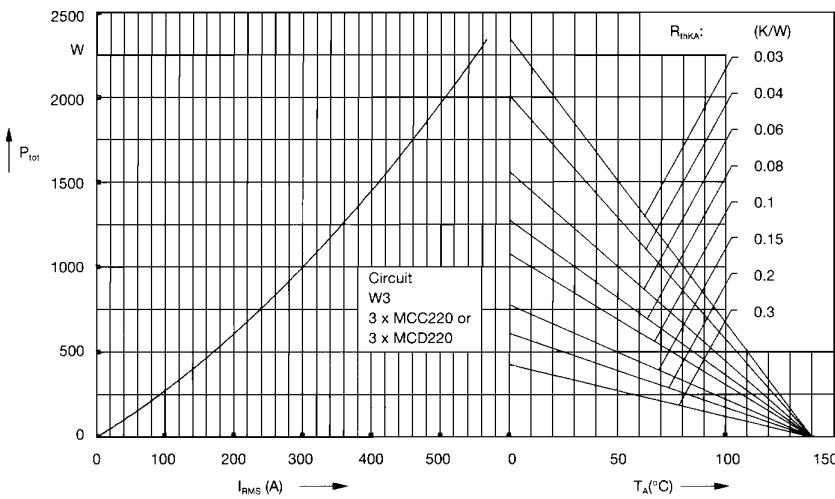


Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature

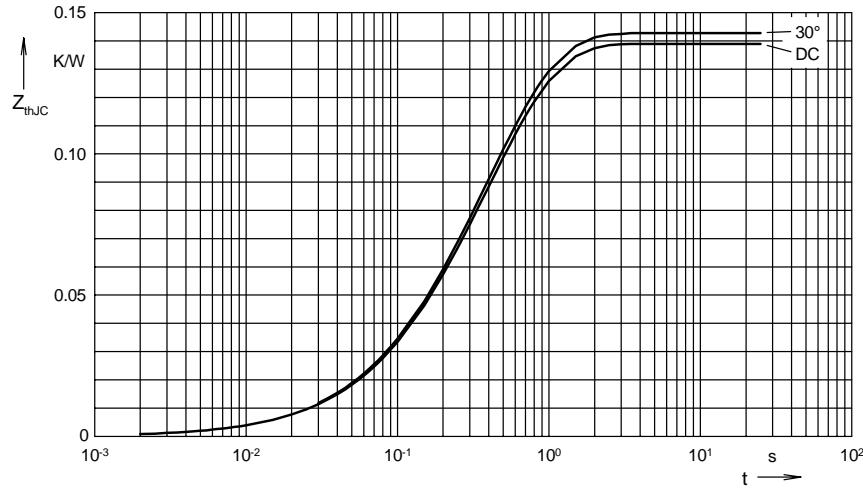


Fig. 8 Transient thermal impedance
junction to case (per thyristor or
diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.139
180°C	0.141
120°C	0.142
60°C	0.142
30°C	0.143

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0037	0.0099
2	0.0177	0.168
3	0.1175	0.456

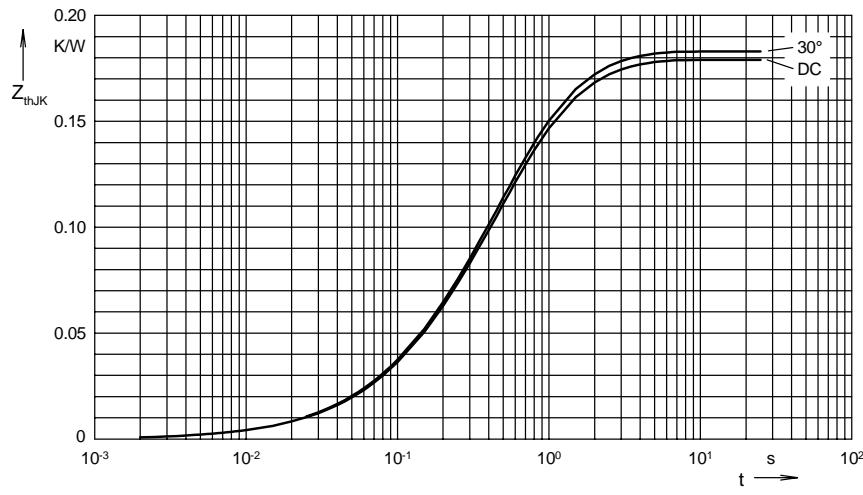


Fig. 9 Transient thermal impedance
junction to heatsink (per thyristor or
diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.179
180°C	0.181
120°C	0.182
60°C	0.183
30°C	0.183

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0037	0.0099
2	0.0177	0.168
3	0.1175	0.456
4	0.04	1.36

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